

ABSTRACT

A method of making a mask is provided to produce a low-cost phase-shift reticle and a low-cost reticle for correction exposure in a short time. Master patterns (PA1-PC1), i.e., enlarged final device patterns are drawn to make a master reticle (MR). Opaque patterns (PA2-PC2) are formed on a substrate (R1) by reduction transfer of the master patterns (PA1-PC1) of the master reticle (MR), and a phase-shift reticle (WR1) is then produced by forming phase shifters (SA-SD). Opaque patterns (PA3-PC3) are formed on the substrate (R2) by reduction transfer of the master patterns (PA1-PC1) of the master reticle (MR) with less exposure than the exposure for the phase-shift reticle (WR1) so that a reticle (WR2) for correction exposure is produced.